

# 4 Mbit Firmware Hub

## SST49LF004B



*Preliminary Specifications*

### FEATURES:

- **4 Mbit SuperFlash memory array for code/data storage**
  - SST49LF004B: 512K x8 (4 Mbit)
- **Conforms to Intel LPC Interface Specification**
  - Supports Single-Byte Firmware Memory Cycle Type
- **Flexible Erase Capability**
  - Uniform 4 KByte sectors
  - Uniform 64 KByte overlay blocks
  - Chip-Erase for PP Mode Only
- **Single 3.0-3.6V Read and Write Operations**
- **Superior Reliability**
  - Endurance: 100,000 Cycles (typical)
  - Greater than 100 years Data Retention
- **Low Power Consumption**
  - Active Read Current: 6 mA (typical)
  - Standby Current: 10  $\mu$ A (typical)
- **Fast Sector-Erase/Byte-Program Operation**
  - Sector-Erase Time: 18 ms (typical)
  - Block-Erase Time: 18 ms (typical)
  - Chip-Erase Time: 70 ms (typical)
  - Byte-Program Time: 14  $\mu$ s (typical)
  - Chip Rewrite Time: 8 seconds (typical)
  - Single-pulse Program or Erase
  - Internal timing generation
- **CMOS and PCI I/O Compatibility**
- **Two Operational Modes**
  - Low Pin Count (LPC) interface mode for in-system operation
  - Parallel Programming (PP) mode for fast production programming
- **Low Pin Count (LPC) Interface Mode**
  - LPC bus interface supporting byte Read and Write
  - 33 MHz clock frequency operation
  - WP# and TBL# pins provide hardware write protect for entire chip and/or top Boot Block
  - Block Locking Registers for individual block Write-Lock and Lock-Down protection
  - JEDEC Standard SDP Command Set
  - Data# Polling and Toggle Bit for End-of-Write detection
  - 5 GPI pins for system design flexibility
  - 4 ID pins for multi-chip selection
- **Parallel Programming (PP) Mode**
  - 11-pin multiplexed address and 8-pin data I/O interface
  - Supports fast In-System or PROM programming for manufacturing
- **Packages Available**
  - 32-lead PLCC
  - 32-lead TSOP (8mm x 14mm)
- **All non-Pb (lead-free) devices are RoHS compliant**

### PRODUCT DESCRIPTION

The SST49LF004B flash memory devices are designed to interface with host controllers (chipsets) that support a low-pin-count (LPC) interface for BIOS applications. The SST49LF004B devices comply with Intel's LPC Interface Specification, supporting single-byte Firmware Memory cycle type.

The SST49LF004B devices are backward compatible to the SST49LF004A Firmware Hub. In this document, FWH mode in the SST49LF004A specification is referenced as the Firmware Memory Read/Write cycle. Two interface modes are supported by the SST49LF004B: LPC mode (Firmware Memory cycle types) for in-system operations and Parallel Programming (PP) mode to interface with programming equipment.

The SST49LF004B flash memory devices are manufactured with SST's proprietary, high-performance SuperFlash technology. The split-gate cell design and thick-oxide tunneling injector attain greater reliability and manufacturability compared with alternative approaches. The SST49LF004B devices significantly improve performance

and reliability, while lowering power consumption. The SST49LF004B devices write (Program or Erase) with a single 3.0-3.6V power supply.

The SST49LF004B use less energy during Erase and Program than alternative flash memory technologies. The total energy consumed is a function of the applied voltage, current and time of application. Since for any given voltage range the SuperFlash technology uses less current to program and has a shorter erase time, the total energy consumed during any Erase or Program operation is less than alternative flash memory technologies.

The SuperFlash technology provides fixed Erase and Program times, independent of the number of Erase/Program cycles that have occurred. This means the system software or hardware does not have to be calibrated or correlated to the cumulative number of Erase cycles as is necessary with alternative flash memory technologies, whose Erase and Program times increase with accumulated Erase/Program cycles.



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The SST49LF004B devices provide a maximum Byte-Program time of 20  $\mu$ sec. The entire memory can be erased and programmed byte-by-byte typically in 8 seconds for the SST49LF004B device, when using status detection features such as Toggle Bit or Data# Polling to indicate the completion of Program operation. To protect against inadvertent writes, the SST49LF004B device employ on-chip hardware and software data protection (SDP) schemes. It is offered with a typical endurance of 100,000 cycles. Data retention is rated at greater than 100 years.

To meet high density, surface mount requirements, the SST49LF004B is offered in both 32-lead PLCC and 32-lead TSOP packages. In addition, SST provides lead-free (non-Pb) package options to address the growing need for non-Pb solutions in electronic components. Non-Pb package version can be obtained by ordering products with a package code suffix of "E" as the environmental attribute in the product part number. See Figures 1 and 2 for pin assignments and Table 1 for pin descriptions.

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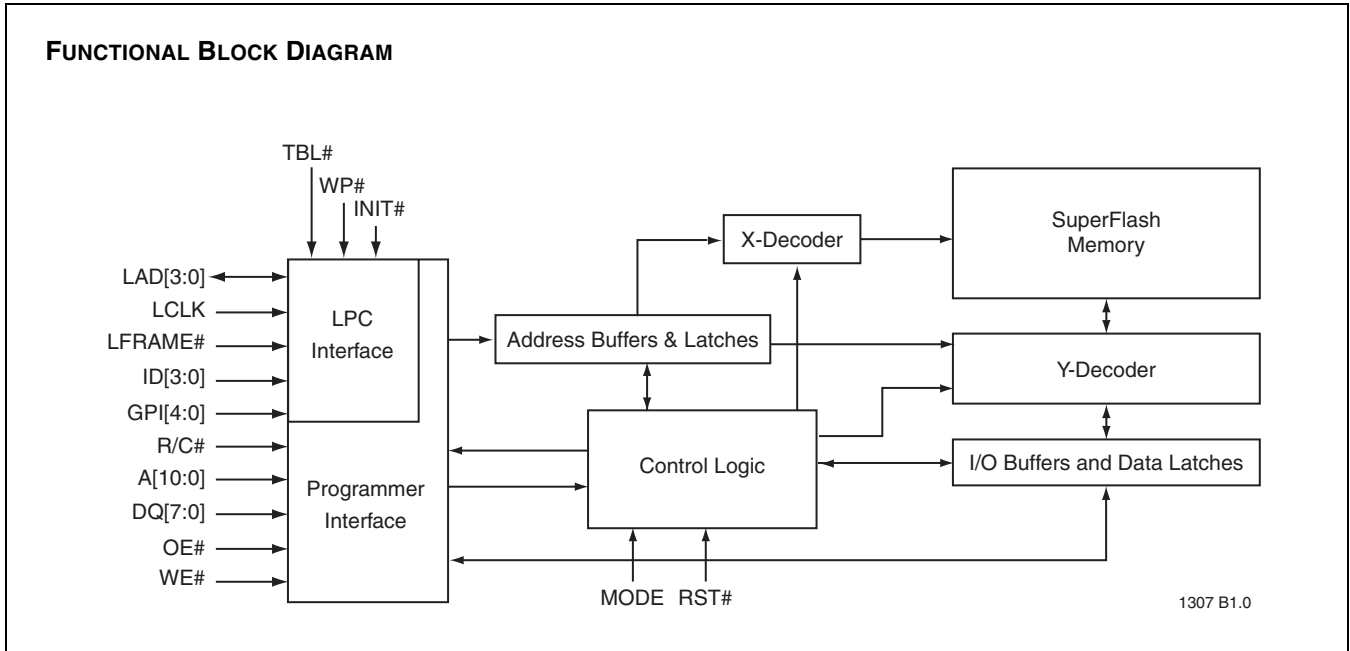
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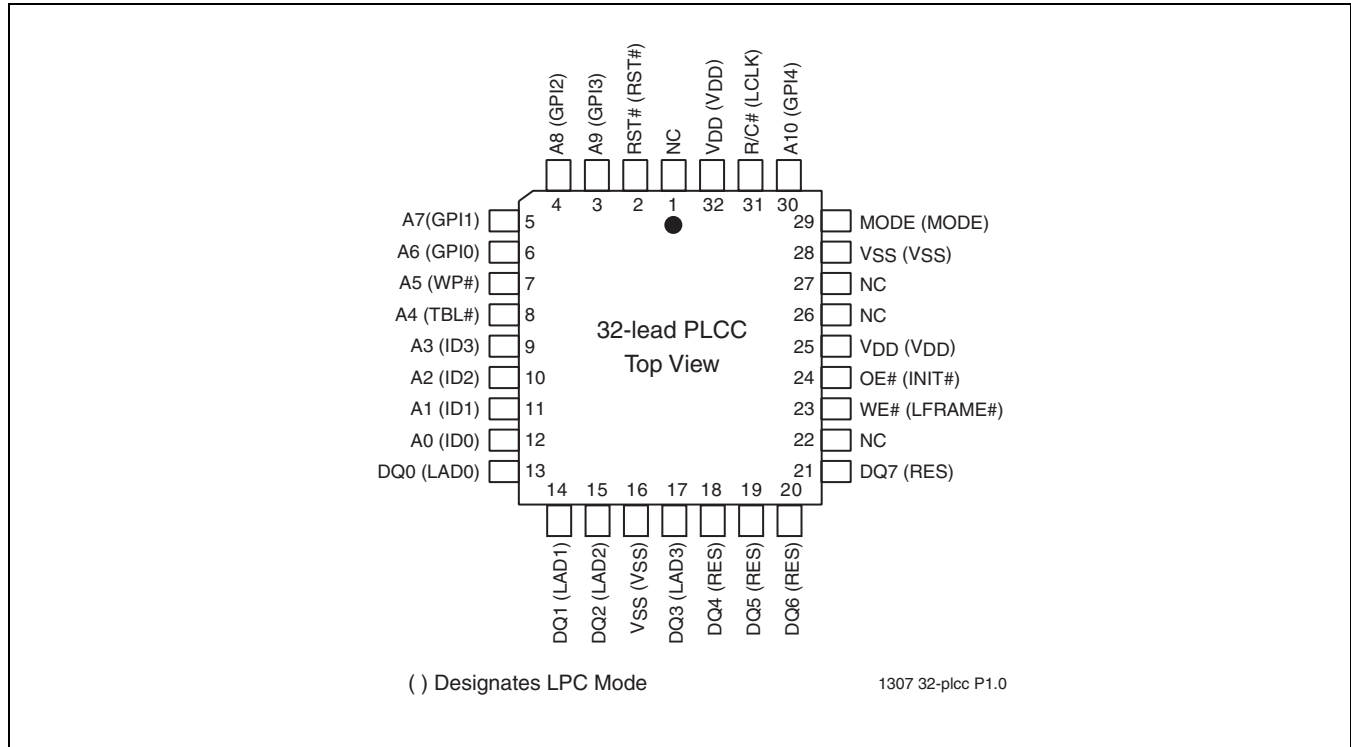


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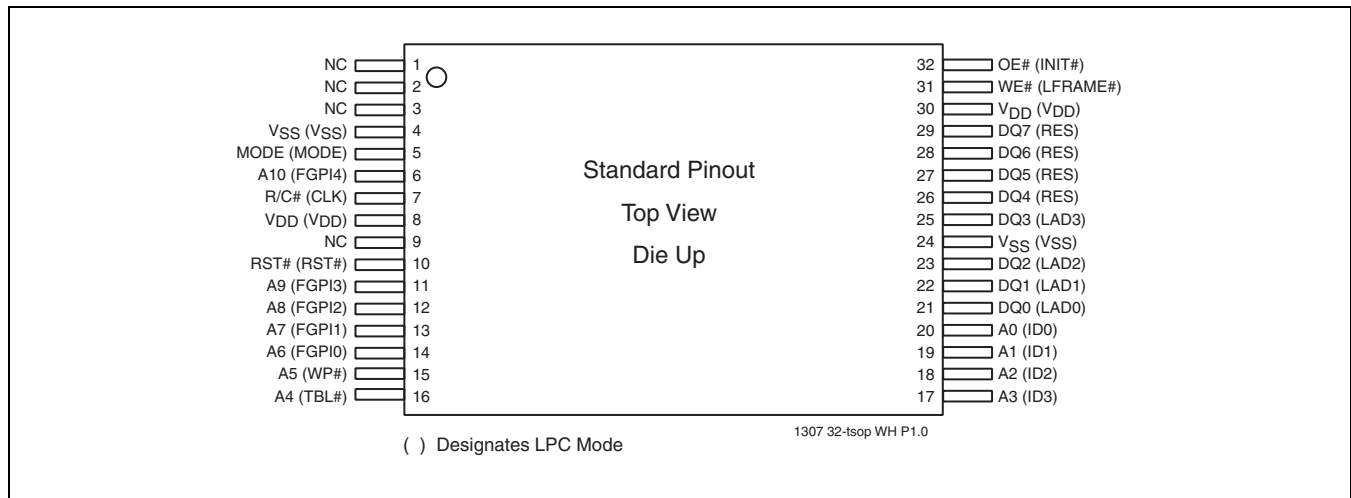
## FUNCTIONAL BLOCKS



**PIN ASSIGNMENTS**



**FIGURE 1: PIN ASSIGNMENTS FOR 32-LEAD PLCC**



**FIGURE 2: PIN ASSIGNMENTS FOR 32-LEAD TSOP**



Preliminary Specifications

**PIN DESCRIPTIONS**

**TABLE 1: PIN DESCRIPTION**

Symbol	Pin Name	Type <sup>1</sup>	Interface		Functions
			PP	LPC	
LCLK	Clock	I		X	To provide a clock input to the control unit. The clock conforms to the PCI specification.
LAD[3:0]	Address and Data	I/O		X	To provide LPC bus information such as addresses and command inputs/outputs to memory.
LFRAME#	Frame	I		X	To indicate start of a data transfer operation; also used to abort an LPC cycle in progress.
MODE	Interface Mode Select	I	X	X	This pin determines which interface is operational. When held high, programmer mode is enabled and when held low, LPC mode is enabled. This pin must be set at power-up or before returning from reset and must not change during device operation. This pin must be held high ( $V_{IH}$ ) for PP mode and low ( $V_{IL}$ ) for LPC mode. This pin is internally pulled-down with a resistor between 20-100 K $\Omega$ .
RST#	Reset	I	X	X	To reset the operation of the device
INIT#	Initialize	I		X	This is the second reset pin for in-system use. This pin functions identically to RST#.
ID[3:0]	Identification Inputs	I		X	These four pins are part of the mechanism that allows multiple parts to be attached to the same bus. The strapping of these pins is used to identify the component. The boot device must have ID[3:0]=0000, all subsequent devices should use sequential count-up strapping. These pins are internally pulled-down with a resistor between 20-100 K $\Omega$ .
GPI[4:0]	General Purpose Inputs	I		X	These individual inputs can be used for additional board flexibility. The state of these pins can be read through GPI_REG (General Purpose Inputs Register). These inputs should be at their desired state before the start of the LPC clock cycle during which the read is attempted, and should remain in place until the end of the Read cycle. Unused GPI pins must not be floated.
TBL#	Top Block Lock	I		X	When low, prevents programming to the boot block sectors at the top of the device memory. When TBL# is high it disables hardware write protection for the top block sectors. This pin cannot be left unconnected.
WP#	Write Protect	I		X	When low, prevents programming to all but the highest addressable blocks. When WP# is high it disables hardware write protection for these blocks. This pin cannot be left unconnected.
R/C#	Row/Column Select	I	X		Select for the Programming interface, this pin determines whether the address pins are pointing to the row addresses, or to the column addresses.
A <sub>10</sub> -A <sub>0</sub>	Address	I	X		Inputs for low-order addresses during Read and Write operations. Addresses are internally latched during a Write cycle. For the programming interface, these addresses are latched by R/C# and share the same pins as the high-order address inputs.
DQ <sub>7</sub> -DQ <sub>0</sub>	Data	I/O	X		To output data during Read cycles and receive input data during Write cycles. Data is internally latched during a Write cycle. The outputs are in tri-state when OE# is high.
OE#	Output Enable	I	X		To gate the data output buffers.
WE#	Write Enable	I	X		To control the Write operations.
RES	Reserved			X	These pins must be left unconnected.
V <sub>DD</sub>	Power Supply	PWR	X	X	To provide power supply (3.0-3.6V)
V <sub>SS</sub>	Ground	PWR	X	X	Circuit ground (0V reference)
NC	No Connection		N/A	N/A	Unconnected pins.

T1.2 1307

1. I = Input, O = Output





### Clock

The LCLK pin accepts a clock input from the host controller.

### Input/Output Communications

The LAD[3:0] pins are used to serially communicate cycle information such as cycle type, cycle direction, ID selection, address, data, and sync fields.

### Input Communication Frame

The LFRAME# pin is used to indicate start of a LPC bus cycle. The pin is also used to abort an LPC bus cycle in progress.

### Interface Mode Select

The MODE pin is used to set the interface mode. If the mode pin is set to logic high, the device is in PP mode. If the mode pin is set low, the device is in the LPC mode. The mode selection pin must be configured prior to device operation. The mode pin is internally pulled down if the pin is left unconnected.

### Reset

A  $V_{IL}$  on INIT# or RST# pin initiates a device reset. INIT# and RST# pins have the same function internally. It is required to drive INIT# or RST# pins low during a system reset to ensure proper CPU initialization. During a Read operation, driving INIT# or RST# pins low deselects the device and places the output drivers, LAD[3:0], in a high impedance state. The reset signal must be held low for a minimum of time  $T_{RSTR}$ . A reset latency occurs if a reset procedure is performed during a Program or Erase operation. See Tables 19 and 20, Reset Timing Parameters, for more information. A device reset during an active Program or Erase operation will abort the operation and memory contents may become invalid due to data being altered or corrupted from an incomplete Erase or Program operation.

### Identification Inputs

These pins are part of a mechanism that allows multiple devices to be attached to the same bus. The strapping of these pins is used to identify the component. The boot device must have ID[3:0] = 0; all subsequent devices should use sequential count-up strapping. These pins are internally pulled-down with a resistor between 20-100  $K\Omega$ .

### General Purpose Inputs

The General Purpose Inputs (GPI[4:0]) can be used as digital inputs for the CPU to read. The GPI register holds the values on these pins. The data on the GPI pins must be stable before the start of a GPI register Read and remain stable until the Read cycle is complete. The pins must be driven low,  $V_{IL}$ , or high,  $V_{IH}$  but not left unconnected (float).

### Write Protect / Top Block Lock

The Top Boot Lock (TBL#) and Write Protect (WP#) pins are provided for hardware write protection of device memory in the SST49LF004B. The TBL# pin is used to write protect 16 boot sectors (64 KByte) at the highest memory address range for the SST49LF004B. The WP# pin write protects the remaining sectors in the flash memory.

An active low signal at the TBL# pin prevents Program and Erase operations of the top boot block. When TBL# pin is held high, the hardware write protection of the top boot block is disabled. The WP# pin serves the same function for the remaining blocks of the device memory. The TBL# and WP# pins write protection functions operate independently of one another. Both TBL# and WP# pins must be set to their required protection states prior to starting a Program or Erase operation. A logic level change occurring at the TBL# or WP# pin during a Program or Erase operation could cause unpredictable results.

### Row / Column Select

The R/C# pin is used to control the multiplex address inputs in Parallel Programming (PP) mode. The column addresses are mapped to the higher internal address ( $A_{18-11}$ ), and the row addresses are mapped to the lower internal addresses ( $A_{10-0}$ ).

### Output Enable

The OE# pin is used to gate the output data buffers in PP mode.

### Write Enable

The WE# pin is used to control the write operations in PP mode.

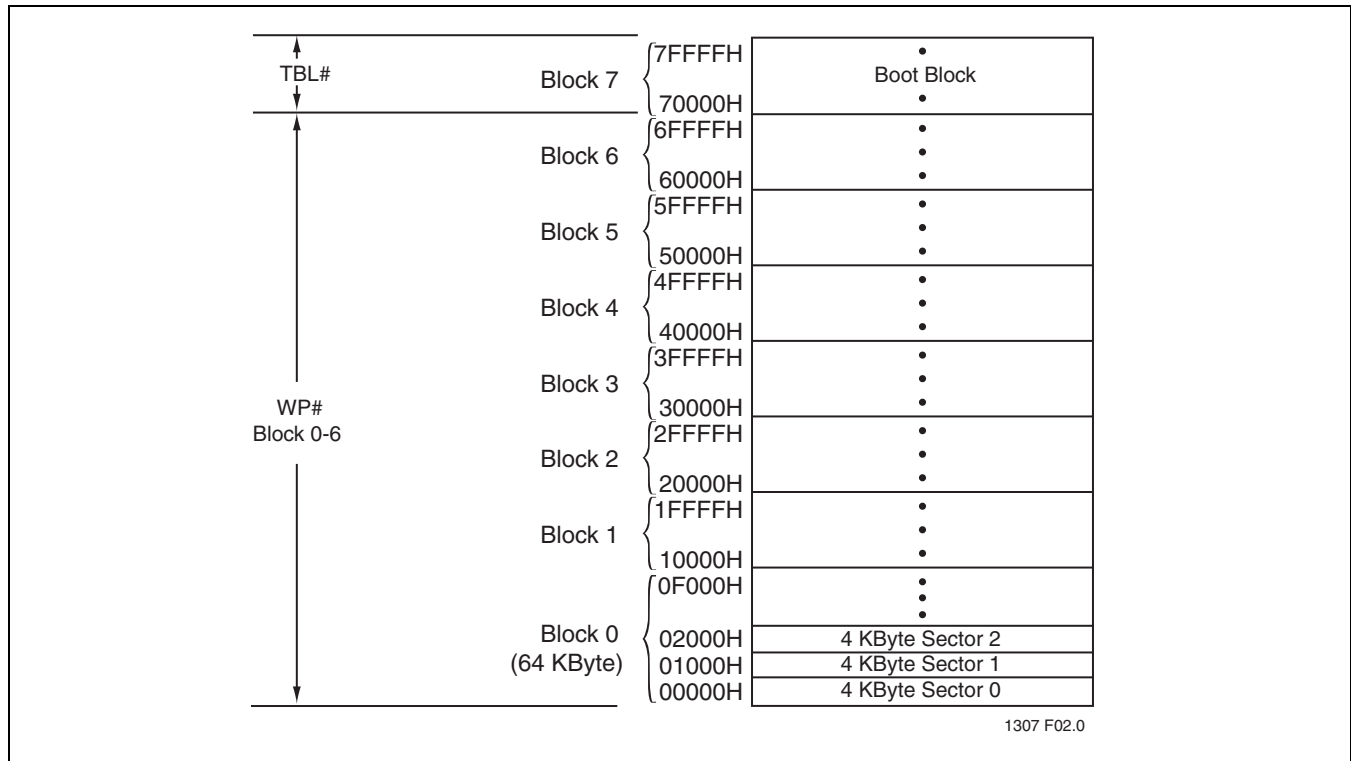
### No Connection

These pins are not connected internally.



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**DEVICE MEMORY MAP**



**FIGURE 3: DEVICE MEMORY MAP**

**DESIGN CONSIDERATIONS**

SST recommends a high frequency 0.1 μF ceramic capacitor to be placed as close as possible between V<sub>DD</sub> and V<sub>SS</sub> less than 1 cm away from the V<sub>DD</sub> pin of the device. Additionally, a low frequency 4.7 μF electrolytic capacitor from V<sub>DD</sub> to V<sub>SS</sub> should be placed within 1 cm of the V<sub>DD</sub> pin. If a socket is used for programming purposes, an additional 1-10 μF should be added next to each socket.

The RST# and INIT# pins must remain stable at V<sub>IH</sub> for the entire duration of an Erase or Program operation. WP# must remain stable at V<sub>IH</sub> for the entire duration of the Erase and Program operations for non-Boot Block sectors. To write data to the top Boot Block sectors, the TBL# pin must also remain stable at V<sub>IH</sub> for the entire duration of the Erase and Program operations.

**PRODUCT IDENTIFICATION**

The Product Identification mode identifies the device as the SST49LF004B and manufacturer as SST.

**TABLE 2: PRODUCT IDENTIFICATION**

	Address		Data
	PP Mode	LPC Mode <sup>1</sup>	
Manufacturer's ID	0000H	FFBC 0000H	BFH
Device ID <sup>2</sup> SST49LF004B	0001H	FFBC 0001H	60H

T2.0 1307

1. Address shown in this column is for boot device only. Address locations should appear elsewhere in the 4 GByte system memory map depending on ID strapping values on ID[3:0] pins when multiple LPC memory devices are used in a system.
2. The device ID for SST49LF004B is the same as SST49LF004A.



## MODE SELECTION

The SST49LF004B flash memory device operates in two distinct interface modes: the LPC mode and the Parallel Programming (PP) mode. The MODE (Interface Mode Select) pin is used to set the interface mode selection. If the MODE pin is set to logic high, the device is in PP mode; while if the MODE pin is set low, the device is in LPC mode. The MODE selection pin must be configured prior to device operation and must not change during operation. If the pin is not connected, by default the Mode pin is internally pulled low and the 49LF00xB will be in LPC operation.

In LPC mode, communication between the Host and the SST49LF004B occurs via the 4-bit I/O communication signals, LAD[3:0] and LFRAME#. The SST49LF004B detects whether it is being accessed via a FWH Read or FWH Write cycle by detecting the START field contents; 91101b is a FWH read cycle and a 1110b indicates a FWH Write cycle.

In PP mode, the device is controlled via the 11 addresses, A<sub>10</sub>-A<sub>0</sub>, and 8 I/O, DQ<sub>7</sub>-DQ<sub>0</sub>, signals. The address inputs are multiplexed in row and column selected by control signal R/C# pin. The row addresses are mapped to the lower internal addresses (A<sub>10-0</sub>), and the column addresses are mapped to the higher internal addresses (A<sub>18-11</sub>). See Figure 3, Device Memory Map, for address assignments.

## LPC MODE

### Device Operation

The LPC mode uses a 5-signal communication interface consisting of one control line, LFRAME#, which is driven by the host to start or abort a bus cycle, and a 4-bit data bus, LAD[3:0], which is used to communicate cycle type, cycle direction, ID selection, address, data and sync fields. The device enters standby mode when LFRAME# is high and no internal operation is in progress.

The SST49LF004B supports single-byte Firmware Memory Read/Write cycles as defined in Intel's Low-Pin-Count Interface Specification. The host drives LFRAME# low for one or more clock cycles to initiate an LPC cycle. The last latched value of LAD[3:0] before LFRAME# is the START value. The START value determines whether the SST49LF004B will respond to a Firmware Memory Read or Firmware Memory Write cycle as defined in Table 3.

**TABLE 3: FIRMWARE MEMORY CYCLES START FIELD DEFINITION**

START Value	Definition
1101	Start of a Firmware Memory Read cycle
1110	Start of a Firmware Memory Write cycle

T3.0 1307

See following sections for details of Firmware Memory cycle types. JEDEC standard SDP (Software Data Protection) Program and Erase command sequences are used to initiate Firmware Memory Program and Erase operations. See Table 9 for a listing of Program and Erase commands. Chip-Erase is only available in PP mode.



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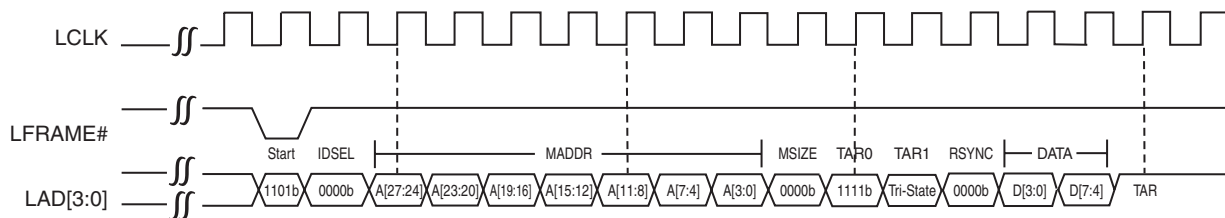
Firmware Memory Read Cycle

TABLE 4: FIRMWARE MEMORY READ CYCLE FIELD DEFINITIONS

Clock Cycle	Field Name	Field Contents LAD[3:0] <sup>1</sup>	LAD[3:0] Direction	Comments
1	START	1101	IN	LFRAME# must be active (low) for the device to respond. Only the last field latched before LFRAME# transitions high will be recognized. The START field contents (1101b) indicate a Firmware Memory Read cycle.
2	IDSEL	0000 to 1111	IN	Indicates which SST49LF004B device should respond. If the IDSEL (ID select) field matches the value of ID[3:0], the device will respond to the LPC bus cycle.
3-9	MADDR	YYYY	IN	These seven clock cycles make up the 28-bit memory address. YYYY is one nibble of the entire address. Addresses are transferred most-significant nibble first.
10	MSIZE	0000 (1 Byte)	IN	The MSIZE field indicates how many bytes will be transferred during multi-byte operations. The SST49LF004B only supports single-byte operation. MSIZE=0000b
11	TAR0	1111	IN then Float	In this clock cycle, the master has driven the bus to all '1's and then floats the bus, prior to the next clock cycle. This is the first part of the bus "turnaround cycle."
12	TAR1	1111 (float)	Float then OUT	The SST49LF004B takes control of the bus during this cycle.
13	RSYNC	0000 (READY)	OUT	During this clock cycle, the device generates a "ready sync" (RSYNC) indicating that the device has received the input data.
14	DATA	ZZZZ	OUT	ZZZZ is the least-significant nibble of the data byte.
15	DATA	ZZZZ	OUT	ZZZZ is the most-significant nibble of the data byte.
16	TAR0	1111	OUT then Float	In this clock cycle, the SST49LF004B drives the bus to all ones and then floats the bus prior to the next clock cycle. This is the first part of the bus "turnaround cycle."
17	TAR1	1111 (float)	Float then IN	The host resumes control of the bus during this cycle.

T4.1 1307

1. Field contents are valid on the rising edge of the present clock cycle.



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FIGURE 4: FIRMWARE MEMORY READ CYCLE WAVEFORM



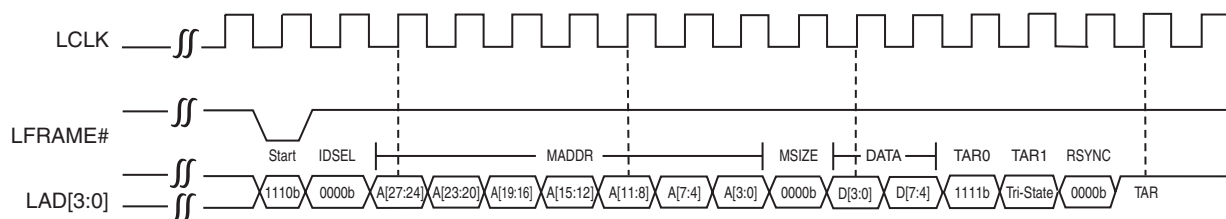
Firmware Memory Write Cycle

TABLE 5: FIRMWARE MEMORY WRITE CYCLE

Clock Cycle	Field Name	Field Contents LAD[3:0] <sup>1</sup>	LAD[3:0] Direction	Comments
1	START	1110	IN	LFRAME# must be active (low) for the device to respond. Only the last field latched before LFRAME# transitions high will be recognized. The START field contents (1110b) indicate a Firmware Memory Write cycle.
2	IDSEL	0000 to 1111	IN	Indicates which SST49LF004B device should respond. If the IDSEL (ID select) field matches the value of ID[3:0], the device will respond to the memory cycle.
3-9	MADDR	YYYY	IN	These seven clock cycles make up the 28-bit memory address. YYYY is one nibble of the entire address. Addresses are transferred most-significant nibble first.
10	MSIZE	0000 (1 Byte)	IN	The MSIZE field indicates how many bytes will be transferred during multi-byte operations. The device only supports single-byte writes. MSIZE=0000b
11	DATA	ZZZZ	IN	ZZZZ is the least-significant nibble of the data byte.
12	DATA	ZZZZ	IN	ZZZZ is the most-significant nibble of the data byte.
13	TAR0	1111	IN then Float	In this clock cycle, the host drives the bus to all '1's and then floats the bus prior to the next clock cycle. This is the first part of the bus "turnaround cycle."
14	TAR1	1111 (float)	Float then OUT	The SST49LF004B takes control of the bus during this cycle.
15	RSYNC	0000	OUT	During this clock cycle, the device generates a "ready sync" (RSYNC) indicating that the device has received the input data.
16	TAR0	1111	OUT then Float	In this clock cycle, the SST49LF004B drives the bus to all '1's and then floats the bus prior to the next clock cycle. This is the first part of the bus "turnaround cycle."
17	TAR1	1111 (float)	Float then IN	The host resumes control of the bus during this cycle.

T5.0 1307

1. Field contents are valid on the rising edge of the present clock cycle.



1307 F04.0

FIGURE 5: FIRMWARE MEMORY WRITE CYCLE WAVEFORM



Preliminary Specifications

### Abort Mechanism

If LFRAME# is driven low for one or more clock cycles after the start of a bus cycle, the cycle will be terminated. The host may drive LAD[3:0] with '1111b' (ABORT nibble) to return the interface to ready mode. The ABORT only affects the current bus cycle. For a multi-cycle command sequence, such as the Erase or Program SDP commands, ABORT doesn't interrupt the entire command sequence, only the current bus cycle of the command sequence. The host can re-send the bus cycle for the aborted command and continue the SDP command sequence after the device is ready again.

### Response to Invalid Fields for Firmware Memory Cycle

During LPC operations the SST49LF004B will not explicitly indicate that it has received invalid field sequences. The response to specific invalid fields or sequences is as follows:

**ID mismatch:** If the IDSEL field does not match ID[3:0], the device will ignore the cycle. See Multiple Device Selection section for details.

**Address out of range:** The address sequence is 7 fields long (28 bits) for Firmware Memory bus cycles, but only A<sub>22</sub> and A<sub>18:A<sub>0</sub></sub> will be decoded by SST49LF004B. Address A<sub>22</sub> has the special function of directing reads and writes to the flash core (A<sub>22</sub>=1) or to the register space (A<sub>22</sub>=0).

**Invalid MSIZE field** If the device receives an invalid MSIZE field during a Firmware Memory Read or Write cycle, the cycle will be ignored and no operation will be attempted. The SST49LF004B will not generate any kind of response in this situation. Invalid size fields for a Firmware Memory cycle are any data other than 0000b.

Once valid START, IDSEL, and MSIZE fields are received, the SST49LF004B will always complete the bus cycle. However, if the device is busy performing a flash Erase or Program operation, no new Write command (memory write or register write) will be executed.

### Multiple Device Selection

Multiple LPC flash devices may be strapped to increase memory densities in a system. The four ID pins, ID[3:0], allow up to 16 devices to be attached to the same bus by using different ID strapping in a system. BIOS support, bus loading, or the attaching bridge may limit this number. The boot device must have an ID of 0000b (determined by ID[3:0]); subsequent devices use incremental numbering. Equal density must be used with multiple devices.

### Multiple Device Selection for Firmware Memory Cycle

For Firmware Memory Read/Write cycles, hardware strapping values on ID[3:0] must match the values in IDSEL field. See Table 6 for multiple device selection configurations. The SST49LF004B will compare the IDSEL field with ID[3:0]'s strapping values. If there is a mismatch, the device will ignore the remainder of the cycle.

TABLE 6: FIRMWARE MEMORY MULTIPLE DEVICE SELECTION CONFIGURATION

Device #	ID[3:0]	IDSEL
0 (Boot device)	0000	0000
1	0001	0001
2	0010	0010
3	0011	0011
4	0100	0100
5	0101	0101
6	0110	0110
7	0111	0111
8	1000	1000
9	1001	1001
10	1010	1010
11	1011	1011
12	1100	1100
13	1101	1101
14	1110	1110
15	1111	1111

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### Write Operation Status Detection

The SST49LF004B device provides two software means to detect the completion of a Write (Program or Erase) cycle, in order to optimize the system Write cycle time. The software detection includes two status bits: Data# Polling, DQ<sub>7</sub>, and Toggle Bit, DQ<sub>6</sub>. The End-of-Write detection mode is incorporated into the Firmware Memory Read cycles. The actual completion of the nonvolatile write is asynchronous with the system. Therefore, either a Data# Polling or Toggle Bit read may be simultaneous with the completion of the Write cycle. If this occurs, the system may possibly get an erroneous result, i.e., valid data may appear to conflict with either DQ<sub>7</sub> or DQ<sub>6</sub>. In order to prevent spurious rejection, if an erroneous result occurs, the software routine should include a loop to read the accessed location an additional two (2) times. If both reads are valid, then the device has completed the Write cycle, otherwise the rejection is valid.

#### Data# Polling

When the SST49LF004B device is in the internal Program operation, any attempt to read DQ<sub>7</sub> will produce the complement of the true data. Once the Program operation is completed, DQ<sub>7</sub> will produce true data. Note that even though DQ<sub>7</sub> may have valid data immediately following the completion of an internal Write operation, the remaining data outputs may still be invalid. Valid data will appear on the entire data bus in subsequent successive Read cycles after an interval of 1  $\mu$ s. During an internal Erase operation, any attempt to read DQ<sub>7</sub> will produce a '0'. Once the internal Erase operation is completed, DQ<sub>7</sub> will produce a '1'. Proper status will not be given using Data# Polling if the address is in the invalid range.

#### Toggle Bit

During the internal Program or Erase operation, any consecutive attempts to read DQ<sub>6</sub> will produce alternating 0s and 1s, i.e., toggling between 0 and 1. When the internal Program or Erase operation is completed, the toggling will stop. Note that even though DQ<sub>6</sub> may have valid data immediately following the completion of an internal Write operation, the remaining data outputs may still be invalid. Valid data will appear on the entire data bus in subsequent successive Read cycles after an interval of 1  $\mu$ s. Proper status will not be given using Toggle Bit if the address is in the invalid range.

### Registers

There are three types of registers available on the SST49LF004B, the General Purpose Inputs register, Block Locking registers, and the JEDEC ID registers. These registers appear at their respective address location in the 4 GByte system memory map. Unused register locations will read as 00H. Any attempt to read or write any register during an internal Write operation will be ignored.

#### General Purpose Inputs Register

The GPI\_REG (General Purpose Inputs Register) passes the state of GPI[4:0] to the outputs. It is recommended that the GPI[4:0] pins are in the desired state before LFRAME# is brought low for the beginning of the bus cycle, and remain in that state until the end of the cycle. There is no default value since this is a pass-through register. The GPI register for the boot device appears at FFBC0100H in the 4 GByte system memory map, and will appear elsewhere if the device is not the boot device. The register is not available to be read when the device is in Erase/Program operation.

#### Block Locking Registers

SST49LF004B provides software controlled lock protection through a set of Block Locking registers. The Block Locking registers are Read/Write registers and are accessible through standard addressable memory locations specified in Table 7 for boot device. These registers will appear elsewhere if the device is not the boot device. Unused register locations will read as 00H.

**Write Lock:** The Write-Lock bit, bit 0, controls the lock state. The default Write status of all blocks after power up is write locked. When bit 0 of the Block Locking register is set, Program and Erase operations for the corresponding block are prevented. Clearing the Write-Lock bit will unprotect the block. The Write-Lock bit must be cleared prior to starting a Program or Erase operation since it is sampled at the beginning of the operation.

The Write-Lock bit functions in conjunction with the hardware Write Lock pin TBL# for the top Boot Block. When TBL# is low, it overrides the software locking scheme. The top Boot Block Locking register does not indicate the state of the TBL# pin.

The Write-Lock bit functions in conjunction with the hardware WP# pin for blocks 0 to 6. When WP# is low, it overrides the software locking scheme. The Block Locking registers do not indicate the state of the WP# pin.



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**Lock Down:** The Lock-Down bit, bit 1, controls the Block Locking registers. The default Lock Down status of all blocks upon power-up is not locked down. Once the Lock-Down bit is set, any future attempted changes to that Block Locking register will be ignored. The Lock-Down bit is only cleared upon a device reset with RST# or

INIT# or power down. Current Lock Down status of a particular block can be determined by reading the corresponding Lock-Down bit.

Once the Lock-Down bit of a block is set, the Write-Lock bits for that block can no longer be modified, and the block is locked down in its current state of write accessibility.

**TABLE 7: BLOCK LOCKING REGISTERS<sup>1</sup>**

Register	Block Size	Protected Memory Address Range	Memory Map Register Address
T_BLOCK_LK	64K	07FFFFH - 070000H	FFBF0002H
T_MINUS01_LK	64K	06FFFFH - 060000H	FFBE0002H
T_MINUS02_LK	64K	05FFFFH - 050000H	FFBD0002H
T_MINUS03_LK	64K	04FFFFH - 040000H	FFBC0002H
T_MINUS04_LK	64K	03FFFFH - 030000H	FFBB0002H
T_MINUS05_LK	64K	02FFFFH - 020000H	FFBA0002H
T_MINUS06_LK	64K	01FFFFH - 010000H	FFB90002H
T_MINUS07_LK	64K	00FFFFH - 000000H	FFB80002H

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1. Default value at power up is 01H

**TABLE 8: BLOCK LOCKING REGISTER BITS**

Reserved Bit [7..2]	Lock-Down Bit [1]	Write-Lock Bit [0]	Lock Status
000000	0	0	Full Access
000000	0	1	Write Locked (Default State at Power-Up)
000000	1	0	Locked Open (Full Access Locked Down)
000000	1	1	Write Locked Down

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**JEDEC ID Registers**

The JEDEC ID registers provide access to the manufacturer and device ID information with a single Read cycle. The JEDEC ID registers for the boot device appear at FFBC0000H and FFBC0001H in the 4 GByte system memory map, and will appear elsewhere if the device is not the boot device. Registers are not available for read when the device is in Erase/Program operation. Unused register location will read as 00H. Refer to Table 2 for product identification information.





## PARALLEL PROGRAMMING MODE

### Device Operation

Commands are used to initiate the memory operation functions of the device. The data portion of the software command sequence is latched on the rising edge of WE#. During the software command sequence the row address is latched on the falling edge of R/C# and the column address is latched on the rising edge of R/C#.

### Read

The Read operation of the SST49LF004B device is controlled by OE#. OE# is the output control and is used to gate data from the output pins. Refer to the Read cycle timing diagram, Figure 11, for further details.

### Reset

A  $V_{IL}$  on RST# pin initiates a device reset.

### Byte-Program Operation

The SST49LF004B device is programmed on a byte-by-byte basis. Before programming, one must ensure that the byte that is being programmed is fully erased. The Byte-Program operation is initiated by executing a four-byte command load sequence for Software Data Protection with address (PA) and data in the last bus cycle. During the Byte-Program operation, the row address ( $A_{10}-A_0$ ) is latched on the falling edge of R/C# and the column Address ( $A_{21}-A_{11}$ ) is latched on the rising edge of R/C#. The data bus is latched on the rising edge of WE#. The Program operation, once initiated, will be completed, within 20  $\mu$ s. See Figure 15 for timing waveforms. During the Program operation, the only valid reads are Data# Polling and Toggle Bit. During the internal Program operation, the host is free to perform additional tasks. Any commands written during the internal Program operation will be ignored.

### Sector-Erase Operation

The Sector-Erase operation allows the system to erase the device on a sector-by-sector basis. The sector architecture is based on uniform sector size of 4 KByte. The Sector-Erase operation is initiated by executing a six-byte command load sequence for Software Data Protection with Sector-Erase command (30H) and sector address (SA) in the last bus cycle. The internal Erase operation begins after the sixth WE# pulse. The End-of-Erase can be determined using either Data# Polling or Toggle Bit methods. See Figure 16 for Sector-Erase timing waveforms. Any commands written during the Sector-Erase operation will be ignored.

### Block-Erase Operation

The Block-Erase operation allows the system to erase the device in any of the 8 uniform 64 KByte blocks for the SST49LF004B. The Block-Erase operation is initiated by executing a six-byte command load sequence for Software Data Protection with Block-Erase command (50H) and block address (BA) in the last bus cycle. The internal Block-Erase operation begins after the sixth WE# pulse. The End-of-Erase can be determined using either Data# Polling or Toggle Bit methods. See Figure 17 for timing waveforms. Any commands written during the Block-Erase operation will be ignored.

### Chip-Erase Operation

The SST49LF004B device provides a Chip-Erase operation only in PP mode, which allows the user to erase the entire memory array to the '1's state. This is useful when the entire device must be quickly erased.

The Chip-Erase operation is initiated by executing a six-byte Software Data Protection command sequence with Chip-Erase command (10H) with address 5555H in the last bus cycle. The internal Erase operation begins with the rising edge of the sixth WE#. During the internal Erase operation, the only valid reads are Toggle Bit or Data# Polling. See Table 10 for the command sequence, Figure 18 for timing diagram. Any commands written during the Chip-Erase operation will be ignored.

### Write Operation Status Detection

The SST49LF004B device provides two software means to detect the completion of a Write (Program or Erase) cycle, in order to optimize the system Write cycle time. The software detection includes two status bits: Data# Polling DQ<sub>7</sub> and Toggle Bit DQ<sub>6</sub>. The End-of-Write detection mode is enabled after the rising edge of WE# which initiates the internal Program or Erase operation.

The actual completion of the nonvolatile write is asynchronous with the system; therefore, either a Data# Polling or Toggle Bit read may be simultaneous with the completion of the Write cycle. If this occurs, the system may possibly get an erroneous result, i.e., valid data may appear to conflict with either DQ<sub>7</sub> or DQ<sub>6</sub>. In order to prevent spurious rejection, if an erroneous result occurs, the software routine should include a loop to read the accessed location an additional two (2) times. If both reads are valid, the device has completed the Write cycle, otherwise the rejection is valid.



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**TABLE 9: OPERATION MODES SELECTION (PP MODE)**

Mode	RST#	OE#	WE#	DQ	Address
Read	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IH</sub>	D <sub>OUT</sub>	A <sub>IN</sub>
Program	V <sub>IH</sub>	V <sub>IH</sub>	V <sub>IL</sub>	D <sub>IN</sub>	A <sub>IN</sub>
Erase	V <sub>IH</sub>	V <sub>IH</sub>	V <sub>IL</sub>	X <sup>1</sup>	Sector or Block address, XXH for Chip-Erase
Reset	V <sub>IL</sub>	X	X	High Z	X
Write Inhibit	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IH</sub>	High Z/D <sub>OUT</sub>	X
Product Identification	V <sub>IH</sub>	V <sub>IL</sub>	V <sub>IH</sub>	Manufacturer's ID (BFH) Device ID <sup>2</sup>	A <sub>18</sub> - A <sub>1</sub> = V <sub>IL</sub> , A <sub>0</sub> = V <sub>IL</sub> A <sub>18</sub> - A <sub>1</sub> = V <sub>IL</sub> , A <sub>0</sub> = V <sub>IH</sub>

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1. X can be V<sub>IL</sub> or V<sub>IH</sub>, but no other value.
2. Device ID = 60H for SST49LF004B

**Data# Polling DQ<sub>7</sub>**

When the SST49LF004B device is in the internal Program operation, any attempt to read DQ<sub>7</sub> will produce the complement of the true data. Once the Program operation is completed, DQ<sub>7</sub> will produce true data. Note that even though DQ<sub>7</sub> may have valid data immediately following the completion of an internal Write operation, the remaining data outputs may still be invalid. Valid data will appear on the entire data bus in subsequent successive Read cycles after an interval of 1 μs. During an internal Erase operation, any attempt to read DQ<sub>7</sub> will produce a '0'. Once the internal Erase operation is completed, DQ<sub>7</sub> will produce a '1'. Data# Polling is valid after the rising edge of the fourth WE# pulse for the Program operation. For Sector-Erase, Block-Erase, or Chip-Erase, the Data# Polling is valid after the rising edge of the sixth WE# pulse. See Figure 13 for Data# Polling timing diagram. Proper status will not be given using Data# Polling if the address is in the invalid range.

**Toggle Bit DQ<sub>6</sub>**

During the internal Program or Erase operation, any consecutive attempts to read DQ<sub>6</sub> will produce alternating '0's and '1's, i.e., toggling between 0 and 1. When the internal Program or Erase operation is completed, the toggling will stop. The device is then ready for the next operation. The Toggle Bit is valid after the rising edge of the fourth WE# pulse for Program operation. For Sector-Erase, Block-Erase or Chip-Erase, the Toggle Bit is valid after the rising edge of the sixth WE# pulse. See Figure 14 for Toggle Bit timing diagram.

**Data Protection (PP Mode)**

The SST49LF004B device provides both hardware and software features to protect nonvolatile data from inadvertent writes.

**Hardware Data Protection**

Noise/Glitch Protection: A WE# pulse of less than 5 ns will not initiate a Write cycle.

V<sub>DD</sub> Power Up/Down Detection: The Write operation is inhibited when V<sub>DD</sub> is less than 1.5V.

Write Inhibit Mode: Forcing OE# low, WE# high will inhibit the Write operation. This prevents inadvertent writes during power-up or power-down.

**Software Data Protection (SDP)**

The SST49LF004B provides the JEDEC approved Software Data Protection scheme for all data alteration operation, i.e., Program and Erase. Any Program operation requires the inclusion of a series of three-byte sequence. The three-byte load sequence is used to initiate the Program operation, providing optimal protection from inadvertent Write operations, e.g., during the system power-up or power down. Any Erase operation requires the inclusion of a five-byte load sequence.



## SOFTWARE COMMAND SEQUENCE

TABLE 10: SOFTWARE COMMAND SEQUENCE

Command Sequence	1st <sup>1</sup> Cycle		2nd <sup>1</sup> Cycle		3rd <sup>1</sup> Cycle		4th <sup>1</sup> Cycle		5th <sup>1</sup> Cycle		6th <sup>1</sup> Cycle	
	Addr <sup>2</sup>	Data	Addr <sup>2</sup>	Data	Addr <sup>2</sup>	Data	Addr <sup>2</sup>	Data	Addr <sup>2</sup>	Data	Addr <sup>2</sup>	Data
Byte-Program	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	A0H	PA <sup>3</sup>	Data				
Sector-Erase	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	80H	YYYY 5555H	AAH	YYYY 2AAAH	55H	SA <sub>x</sub> <sup>4</sup>	30H
Block-Erase	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	80H	YYYY 5555H	AAH	YYYY 2AAAH	55H	BA <sub>x</sub> <sup>5</sup>	50H
Chip-Erase <sup>6</sup>	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	80H	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	10H
Software ID Entry <sup>7,8</sup>	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	90H	Read ID					
Software ID Exit <sup>9</sup>	XXXX XXXXH	F0H										
Software ID Exit <sup>9</sup>	YYYY 5555H	AAH	YYYY 2AAAH	55H	YYYY 5555H	F0H						

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1. LPC mode use consecutive Write cycles to complete a command sequence; PP mode use consecutive bus cycles to complete a command sequence.
2. YYYY = A[31:16]. In LPC mode, during SDP command sequence, YYYY must be within valid memory address range, see Address out of range section for details. In PP mode, YYYY can be V<sub>IL</sub> or V<sub>IH</sub>, but no other value.
3. PA = Program Byte address
4. SA<sub>x</sub> for Sector-Erase Address
5. BA<sub>x</sub> for Block-Erase Address
6. Chip-Erase is supported in PP mode only
7. SST Manufacturer's ID = BFH, is read with A<sub>18</sub>-A<sub>0</sub> = 0.  
With A<sub>18</sub>-A<sub>1</sub> = 0; 49LF004B Device ID = 60H, is read with A<sub>0</sub> = 1.
8. The device does not remain in Software Product ID mode if powered down.
9. Both Software ID Exit operations are equivalent



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**ELECTRICAL SPECIFICATIONS**

The AC and DC specifications for the LPC interface signals (LA0[3:0], LFRAME, LCLK and RST#) are defined in Section 4.2.2.4 of the PCI local bus specification, Rev. 2.1. Refer to Table 11 for the DC voltage and current specifications. Refer to Tables 16 through 22 for the AC timing specifications for Clock, Read, Write, and Reset operations.

**Absolute Maximum Stress Ratings** (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Temperature Under Bias .....	-55°C to +125°C
Storage Temperature .....	-65°C to +150°C
D.C. Voltage on Any Pin to Ground Potential .....	-0.5V to V <sub>DD</sub> +0.5V
Transient Voltage (<20 ns) on Any Pin to Ground Potential <sup>1</sup> .....	-2.0V to V <sub>DD</sub> +2.0V
Package Power Dissipation Capability (T <sub>A</sub> =25°C) .....	1.0W
Surface Mount Solder Reflow Temperature <sup>2</sup> .....	260°C for 10 seconds
Output Short Circuit Current <sup>3</sup> .....	50 mA

1. Do not violate processor or chipset limitations on the INIT# pin
2. Excluding certain with-Pb 32-PLCC units, all packages are 260°C capable in both non-Pb and with-Pb solder versions. Certain with-Pb 32-PLCC package types are capable of 240°C for 10 seconds; please consult the factory for the latest information.
3. Outputs shorted for no more than one second. No more than one output shorted at a time.

**OPERATING RANGE**

Range	Ambient Temp	V <sub>DD</sub>
Commercial	0°C to +85°C	3.0-3.6V

**AC CONDITIONS OF TEST<sup>1</sup>**

Input Rise/Fall Time .....	3 ns
Output Load .....	C <sub>L</sub> = 30 pF
See Figures 21 and 22	

1. LPC interface signals use PCI load test condition



DC Characteristics

TABLE 11: DC OPERATING CHARACTERISTICS (ALL INTERFACES)

Symbol	Parameter	Limits			Test Conditions
		Min	Max	Units	
I <sub>DD</sub> <sup>1</sup>	Active V <sub>DD</sub> Current				LCLK (LPC mode) and Address Input (PP mode)=V <sub>ILT</sub> /V <sub>IHT</sub> at f=33 MHz (LPC mode) or 1/TRC <sub>min</sub> (PP mode) All other inputs=V <sub>IL</sub> or V <sub>IH</sub>
	Read Write <sup>2</sup>		12 30	mA mA	All outputs = open, V <sub>DD</sub> =V <sub>DD</sub> Max See Note 2
I <sub>SB</sub>	Standby V <sub>DD</sub> Current (LPC Interface)		100	μA	LCLK (LPC mode) and Address Input (PP mode)=V <sub>ILT</sub> /V <sub>IHT</sub> at f=33 MHz (LPC mode) or 1/TRC <sub>min</sub> (PP mode) LFRAME#=0.9 V <sub>DD</sub> , f=33 MHz, CE#=0.9 V <sub>DD</sub> , V <sub>DD</sub> =V <sub>DD</sub> Max, All other inputs ≥ 0.9 V <sub>DD</sub> or ≤ 0.1 V <sub>DD</sub>
I <sub>RY</sub> <sup>3</sup>	Input Current for Mode and ID[3:0] pins		10	mA	LCLK (LPC mode) and Address Input (PP mode)=V <sub>ILT</sub> /V <sub>IHT</sub> at f=33 MHz (LPC mode) or 1/TRC <sub>min</sub> (PP mode) LFRAME#=V <sub>IL</sub> , f=33 MHz, V <sub>DD</sub> =V <sub>DD</sub> Max All other inputs ≥ 0.9 V <sub>DD</sub> or ≤ 0.1 V <sub>DD</sub>
I <sub>I</sub>	Input Leakage Current for Mode and ID[3:0] pins		200	μA	V <sub>IN</sub> =GND to V <sub>DD</sub> , V <sub>DD</sub> =V <sub>DD</sub> Max
I <sub>LI</sub>	Input Leakage Current		1	μA	V <sub>IN</sub> =GND to V <sub>DD</sub> , V <sub>DD</sub> =V <sub>DD</sub> Max
I <sub>LO</sub>	Output Leakage Current		1	μA	V <sub>OUT</sub> =GND to V <sub>DD</sub> , V <sub>DD</sub> =V <sub>DD</sub> Max
V <sub>IHI</sub>	INIT# Input High Voltage	1.1	V <sub>DD</sub> +0.5	V	V <sub>DD</sub> =V <sub>DD</sub> Max
V <sub>ILI</sub>	INIT# Input Low Voltage	-0.5	0.4	V	V <sub>DD</sub> =V <sub>DD</sub> Min
V <sub>IL</sub>	Input Low Voltage	-0.5	0.3 V <sub>DD</sub>	V	V <sub>DD</sub> =V <sub>DD</sub> Min
V <sub>IH</sub>	Input High Voltage	0.5 V <sub>DD</sub>	V <sub>DD</sub> +0.5	V	V <sub>DD</sub> =V <sub>DD</sub> Max
V <sub>OL</sub>	Output Low Voltage		0.1 V <sub>DD</sub>	V	
V <sub>OH</sub>	Output High Voltage	0.9 V <sub>DD</sub>		V	

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1. I<sub>DD</sub> active while a Read or Write (Program or Erase) operation is in progress.
2. For PP mode: OE# = WE# = V<sub>IH</sub>; For LPC mode: f = 1/TRC<sub>min</sub>, LFRAME# = V<sub>IH</sub>.
3. The device is in Ready mode when no activity is on the LPC bus.

TABLE 12: RECOMMENDED SYSTEM POWER-UP TIMINGS

Symbol	Parameter	Minimum	Units
T <sub>PU-READ</sub> <sup>1</sup>	Power-up to Read Operation	100	μs
T <sub>PU-WRITE</sub> <sup>1</sup>	Power-up to Write Operation	100	μs

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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter

TABLE 13: PIN CAPACITANCE (V<sub>DD</sub>=3.3V, T<sub>A</sub>=25 °C, f=1 Mhz, other pins open)

Parameter	Description	Test Condition	Maximum
C <sub>I/O</sub> <sup>1</sup>	I/O Pin Capacitance	V <sub>I/O</sub> =0V	12 pF
C <sub>IN</sub> <sup>1</sup>	Input Capacitance	V <sub>IN</sub> =0V	12 pF

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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.



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**TABLE 14: RELIABILITY CHARACTERISTICS**

Symbol	Parameter	Minimum Specification	Units	Test Method
$N_{END}^1$	Endurance	10,000	Cycles	JEDEC Standard A117
$T_{DR}^1$	Data Retention	100	Years	JEDEC Standard A103
$I_{LTH}^1$	Latch Up	$100 + I_{DD}$	mA	JEDEC Standard 78

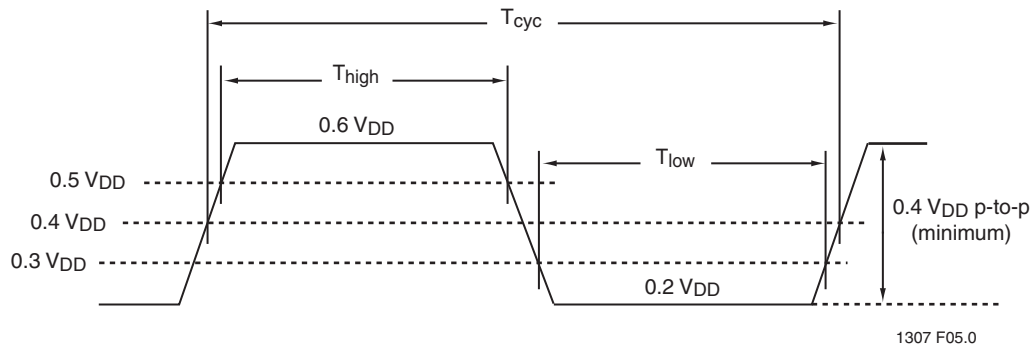
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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

**TABLE 15: CLOCK TIMING PARAMETERS (LPC MODE)**

Symbol	Parameter	Min	Max	Units
$T_{CYC}$	LCLK Cycle Time	30		ns
$T_{HIGH}$	LCLK High Time	11		ns
$T_{LOW}$	LCLK Low Time	11		ns
-	LCLK Slew Rate (peak-to-peak)	1	4	V/ns
-	RST# or INIT# Slew Rate	50		mV/ns

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**FIGURE 6: LCLK WAVEFORM (LPC MODE)**



AC Characteristics (LPC Mode)

TABLE 16: READ/WRITE CYCLE TIMING PARAMETERS,  $V_{DD}=3.0-3.6V$  (LPC MODE)

Symbol	Parameter	Min	Max	Units
$T_{CYC}$	Clock Cycle Time	30		ns
$T_{SU}$	Data Set Up Time to Clock Rising	7		ns
$T_{DH}$	Clock Rising to Data Hold Time	0		ns
$T_{VAL}^1$	Clock Rising to Data Valid	2	11	ns
$T_{BP}$	Byte Programming Time		20	$\mu s$
$T_{SE}$	Sector-Erase Time		25	ms
$T_{BE}$	Block-Erase Time		25	ms
$T_{ON}$	Clock Rising to Active (Float to Active Delay)	2		ns
$T_{OFF}$	Clock Rising to Inactive (Active to Float Delay)		28	ns

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1. Minimum and maximum times have different loads. See PCI spec

TABLE 17: AC INPUT/OUTPUT SPECIFICATIONS (LPC MODE)

Symbol	Parameter	Min	Max	Units	Conditions
$I_{OH}(AC)$	Switching Current High  (Test Point)	$-12 V_{DD}$	Equation C <sup>1</sup>	mA	$0 < V_{OUT} \leq 0.3V_{DD}$
		$-17.1(V_{DD}-V_{OUT})$		mA	$0.3V_{DD} < V_{OUT} < 0.9V_{DD}$
				mA	$0.7V_{DD} < V_{OUT} < V_{DD}$
			$-32 V_{DD}$	mA	$V_{OUT} = 0.7V_{DD}$
$I_{OL}(AC)$	Switching Current Low  (Test Point)	$16 V_{DD}$	Equation D <sup>1</sup>	mA	$V_{DD} > V_{OUT} \geq 0.6V_{DD}$
		$26.7 V_{OUT}$		mA	$0.6V_{DD} > V_{OUT} > 0.1V_{DD}$
				mA	$0.18V_{DD} > V_{OUT} > 0$
			$38 V_{DD}$	mA	$V_{OUT} = 0.18V_{DD}$
$I_{CL}$	Low Clamp Current	$-25+(V_{IN}+1)/0.015$		mA	$-3 < V_{IN} \leq -1$
$I_{CH}$	High Clamp Current	$25+(V_{IN}-V_{DD}-1)/0.015$		mA	$V_{DD}+4 > V_{IN} \geq V_{DD}+1$
slewr	Output Rise Slew Rate	1	4	V/ns	$0.2V_{DD}-0.6V_{DD}$ load
slewf	Output Fall Slew Rate	1	4	V/ns	$0.6V_{DD}-0.2V_{DD}$ load

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1. See PCI spec.

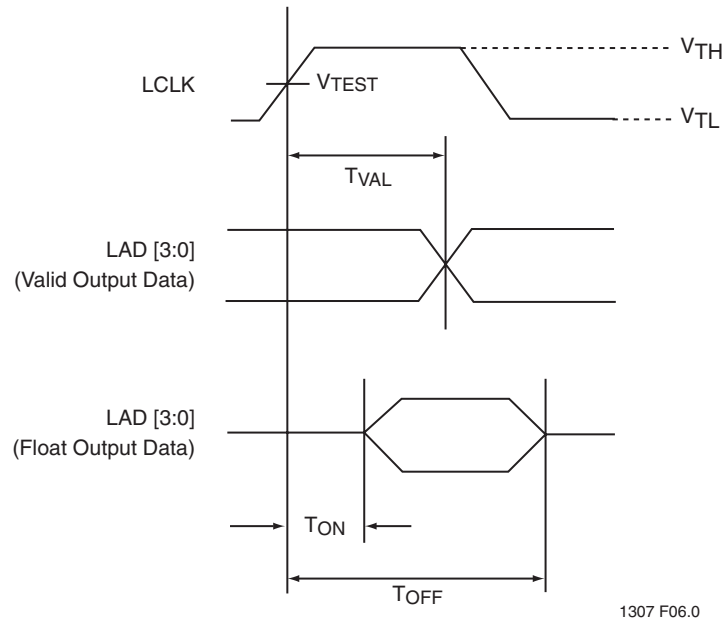


FIGURE 7: OUTPUT TIMING PARAMETERS (LPC MODE)

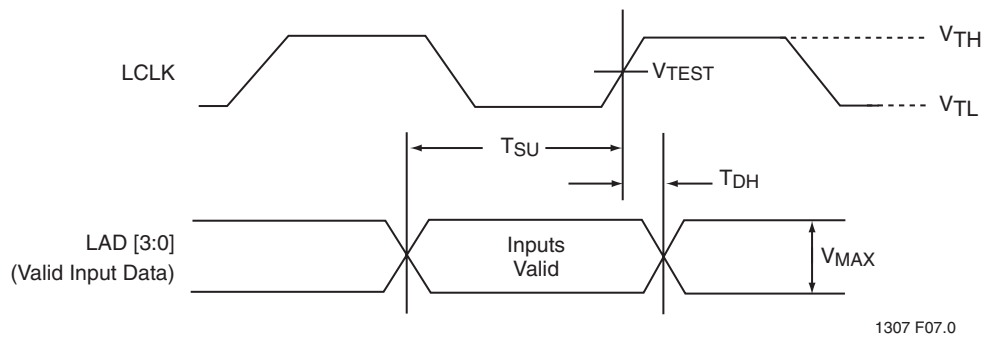


FIGURE 8: INPUT TIMING PARAMETERS (LPC MODE)



**TABLE 18: INTERFACE MEASUREMENT CONDITION PARAMETERS (LPC MODE)**

Symbol	Value	Units
$V_{TH}^1$	0.6 $V_{DD}$	V
$V_{TL}^1$	0.2 $V_{DD}$	V
$V_{TEST}$	0.4 $V_{DD}$	V
$V_{MAX}^1$	0.4 $V_{DD}$	V
Input Signal Edge Rate	1	V/ns

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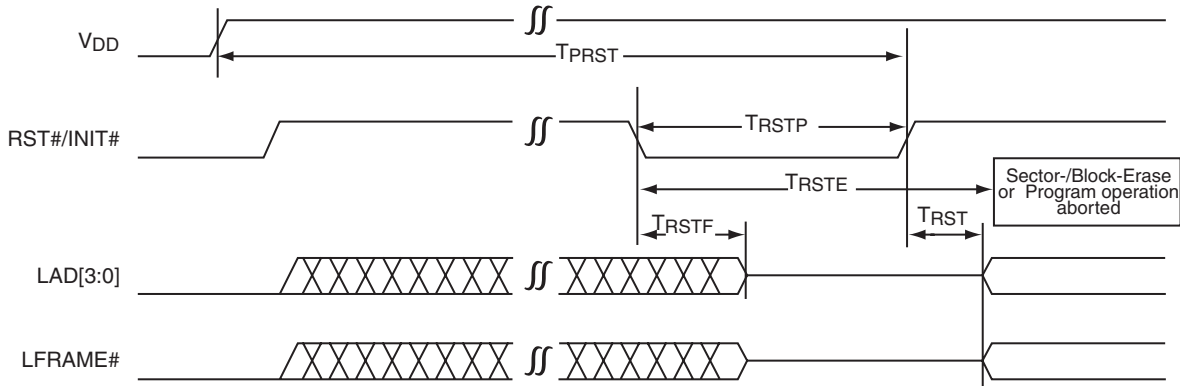
- The input test environment is done with 0.1  $V_{DD}$  of overdrive over  $V_{IH}$  and  $V_{IL}$ . Timing parameters must be met with no more overdrive than this.  $V_{MAX}$  specifies the maximum peak-to-peak waveform allowed for measuring input timing. Production testing may use different voltage values, but must correlate results back to these parameters.

**TABLE 19: RESET TIMING PARAMETERS,  $V_{DD}=3.0-3.6V$  (LPC MODE)**

Symbol	Parameter	Min	Max	Units
$T_{PRST}$	$V_{DD}$ stable to Reset High	100		$\mu s$
$T_{RSTP}$	RST# Pulse Width	100		ns
$T_{RSTF}$	RST# Low to Output Float		48	ns
$T_{RST}^1$	RST# High to LFRAME# Low	5		LCLK cycles
$T_{RSTE}$	RST# Low to reset during Sector-/Block-Erase or Program		10	$\mu s$

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- There will be a latency due to  $T_{RSTE}$  if a reset procedure is performed during a Program or Erase operation,



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**FIGURE 9: RESET TIMING DIAGRAM (LPC MODE)**



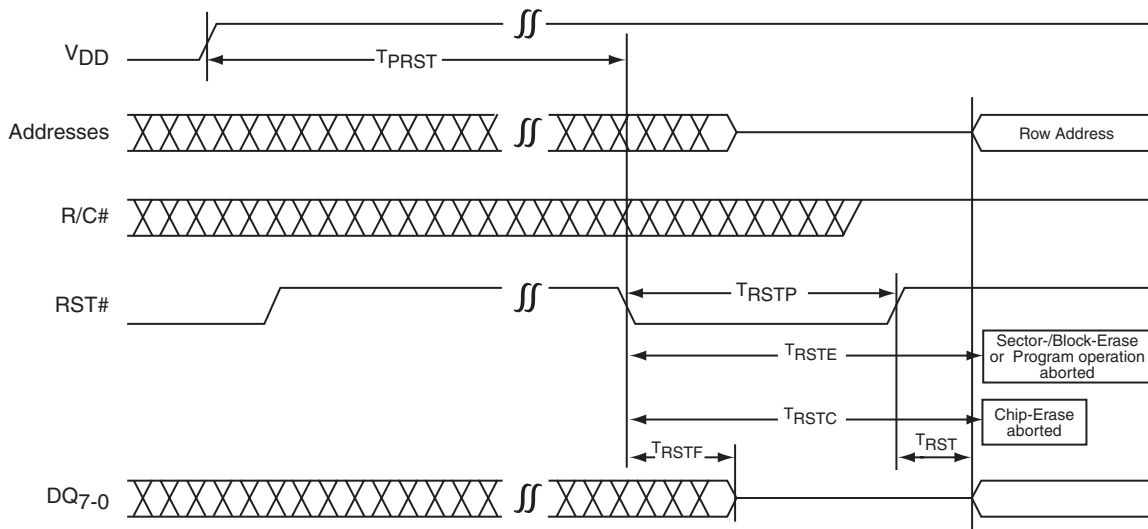
Preliminary Specifications

**TABLE 20: RESET TIMING PARAMETERS,  $V_{DD}=3.0-3.6V$  (PP MODE)**

Symbol	Parameter	Min	Max	Units
$T_{PRST}$	$V_{DD}$ stable to Reset Low	1		ms
$T_{RSTP}$	RST# Pulse Width	100		ns
$T_{RSTF}$	RST# Low to Output Float		48	ns
$T_{RST}^1$	RST# High to Row Address Setup	1		$\mu s$
$T_{RSTE}$	RST# Low to reset during Sector-/Block-Erase or Program		10	$\mu s$
$T_{RSTC}$	RST# Low to reset during Chip-Erase		50	$\mu s$

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1. There will be a reset latency of  $T_{RSTE}$  or  $T_{RSTC}$  if a reset procedure is performed during a programming or erase operational.



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**FIGURE 10: RESET TIMING DIAGRAM (PP MODE)**



AC Characteristics (PP Mode)

TABLE 21: READ CYCLE TIMING PARAMETERS,  $V_{DD}=3.0-3.6V$  (PP MODE)

Symbol	Parameter	Min	Max	Units
$T_{RC}$	Read Cycle Time	270		ns
$T_{RST}$	RST# High to Row Address Setup	1		$\mu s$
$T_{AS}$	R/C# Address Set-up Time	45		ns
$T_{AH}$	R/C# Address Hold Time	45		ns
$T_{AA}$	Address Access Time		120	ns
$T_{OE}$	Output Enable Access Time		60	ns
$T_{OLZ}$	OE# Low to Active Output	0		ns
$T_{OHZ}$	OE# High to High-Z Output		35	ns
$T_{OH}$	Output Hold from Address Change	0		ns

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TABLE 22: PROGRAM/ERASE CYCLE TIMING PARAMETERS,  $V_{DD}=3.0-3.6V$  (PP MODE)

Symbol	Parameter	Min	Max	Units
$T_{RST}$	RST# High to Row Address Setup	1		$\mu s$
$T_{AS}$	R/C# Address Setup Time	45		ns
$T_{AH}$	R/C# Address Hold Time	45		ns
$T_{CWH}$	R/C# to Write Enable High Time	50		ns
$T_{OES}$	OE# High Setup Time	20		ns
$T_{OEH}$	OE# High Hold Time	20		ns
$T_{OEP}$	OE# to Data# Polling Delay		60	ns
$T_{OET}$	OE# to Toggle Bit Delay		60	ns
$T_{WP}$	WE# Pulse Width	100		ns
$T_{WPH}$	WE# Pulse Width High	100		ns
$T_{DS}$	Data Setup Time	50		ns
$T_{DH}$	Data Hold Time	5		ns
$T_{IDA}$	Software ID Access and Exit Time		150	ns
$T_{BP}$	Byte Programming Time		20	$\mu s$
$T_{SE}$	Sector-Erase Time		25	ms
$T_{BE}$	Block-Erase Time		25	ms
$T_{SCE}$	Chip-Erase Time		100	ms

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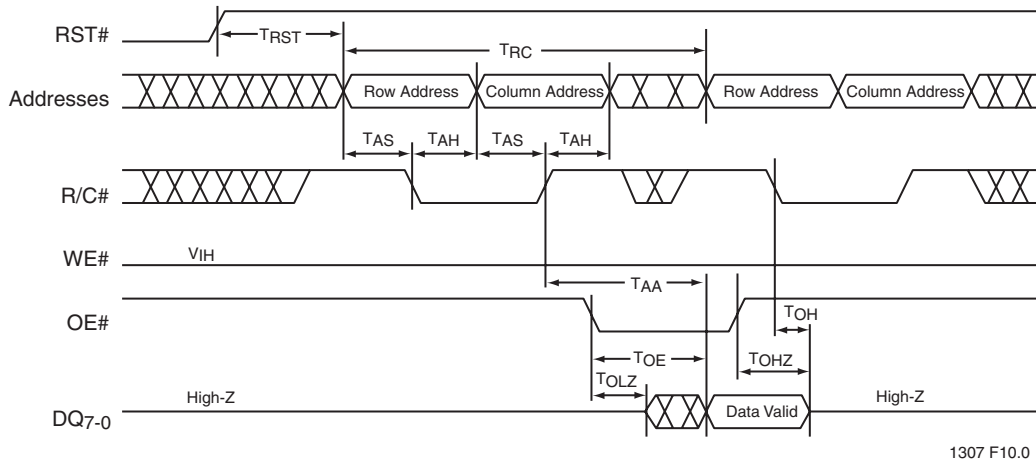


FIGURE 11: READ CYCLE TIMING DIAGRAM (PP MODE)

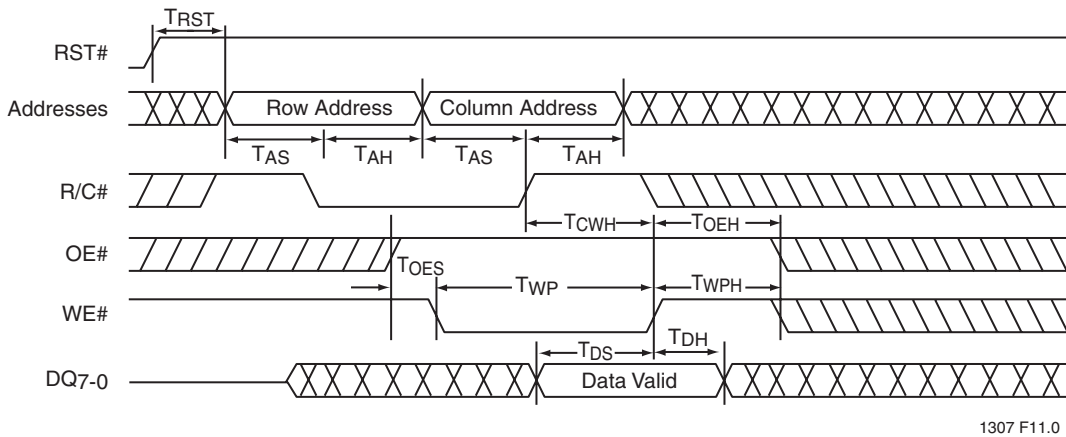
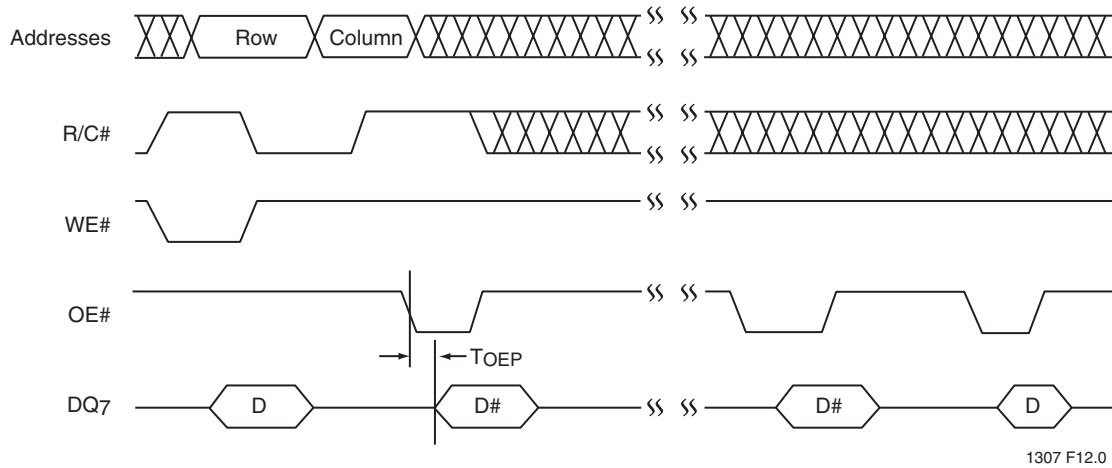
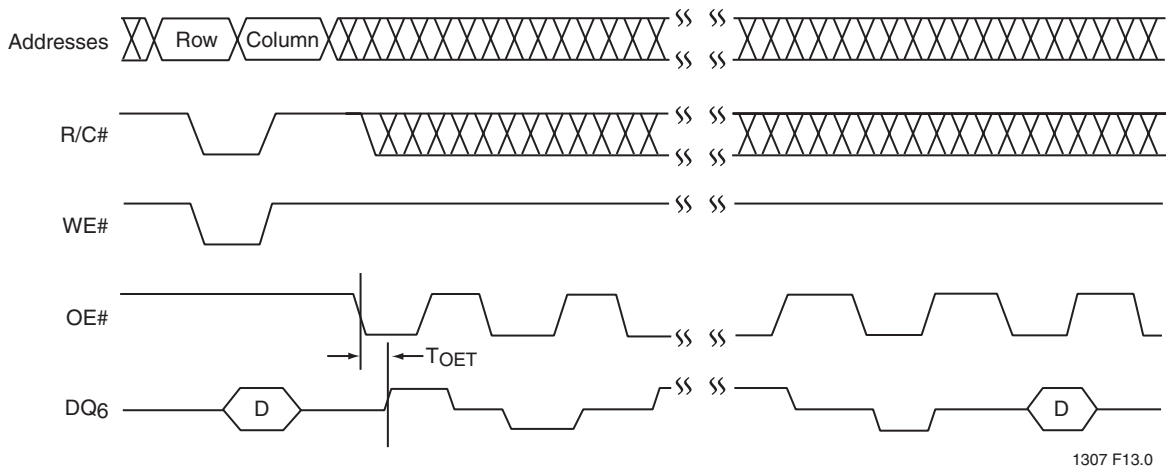


FIGURE 12: WRITE CYCLE TIMING DIAGRAM (PP MODE)



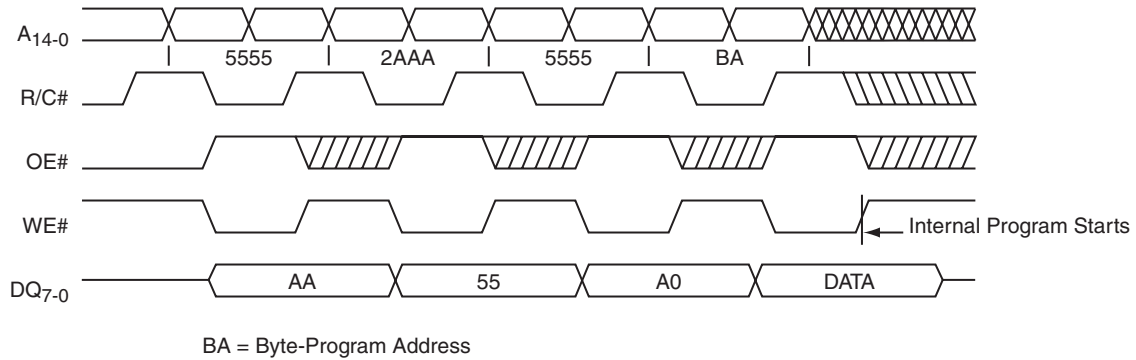
**FIGURE 13: DATA# POLLING TIMING DIAGRAM (PP MODE)**



**FIGURE 14: TOGGLE BIT TIMING DIAGRAM (PP MODE)**

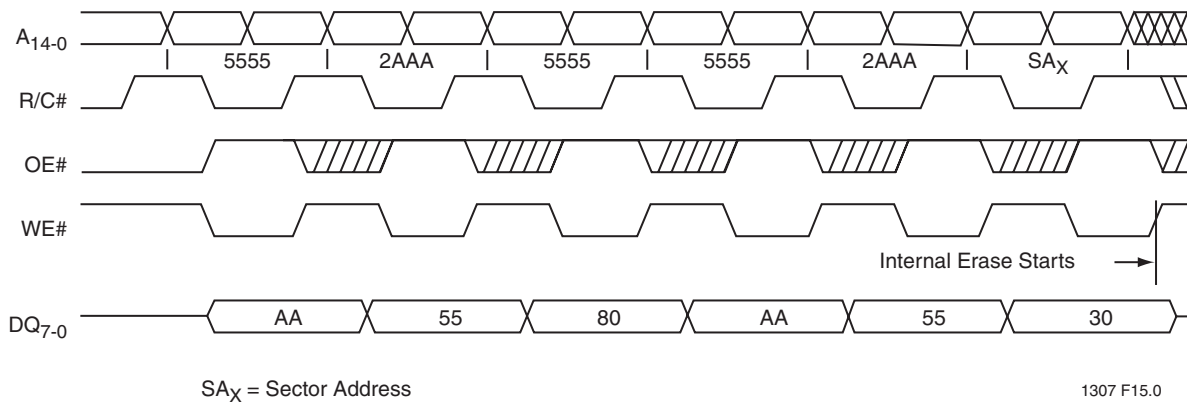


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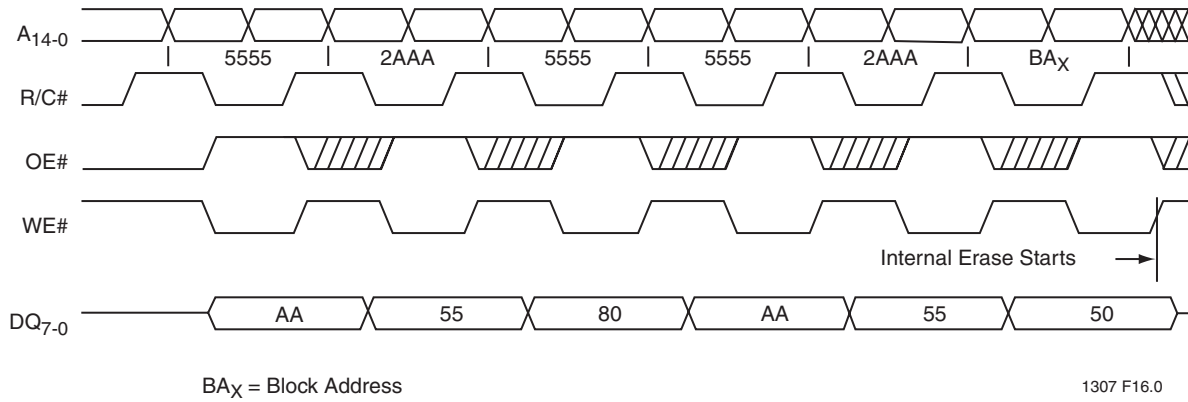
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FIGURE 15: BYTE-PROGRAM TIMING DIAGRAM (PP MODE)



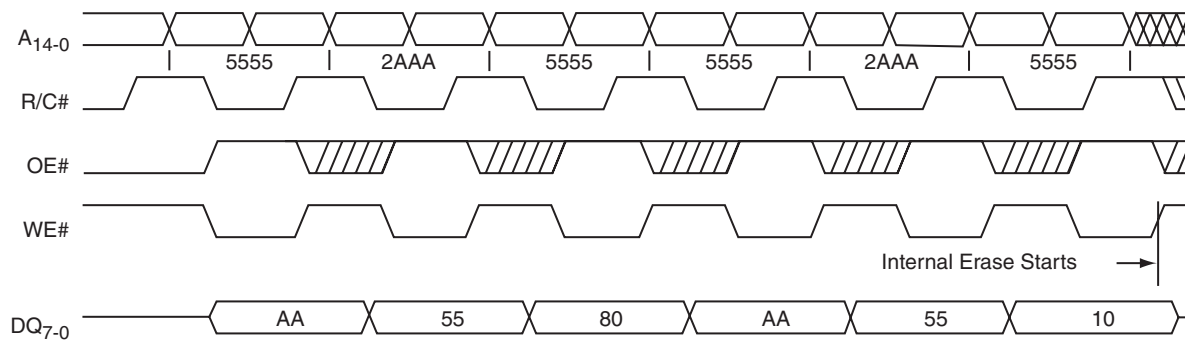
1307 F15.0

FIGURE 16: SECTOR-ERASE TIMING DIAGRAM (PP MODE)



1307 F16.0

FIGURE 17: BLOCK-ERASE TIMING DIAGRAM (PP MODE)

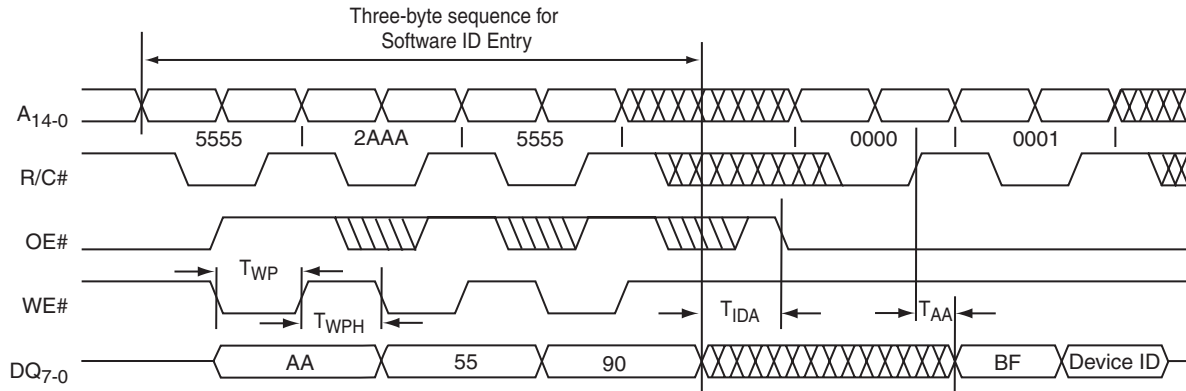


1307 F17.0

FIGURE 18: CHIP-ERASE TIMING DIAGRAM (PP MODE)



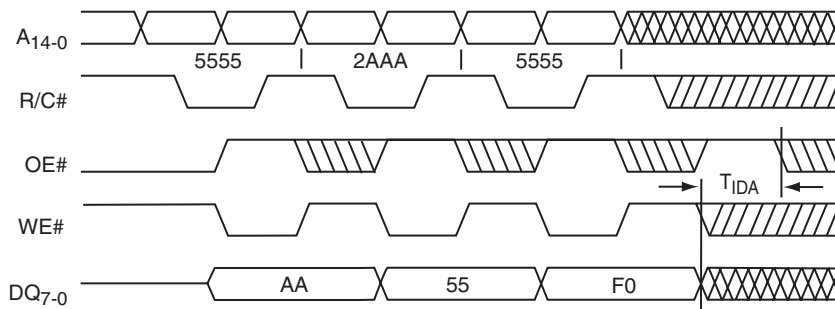
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Device ID = 60H for SST49LF004B

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FIGURE 19: SOFTWARE ID ENTRY AND READ (PP MODE)



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FIGURE 20: SOFTWARE ID EXIT (PP MODE)



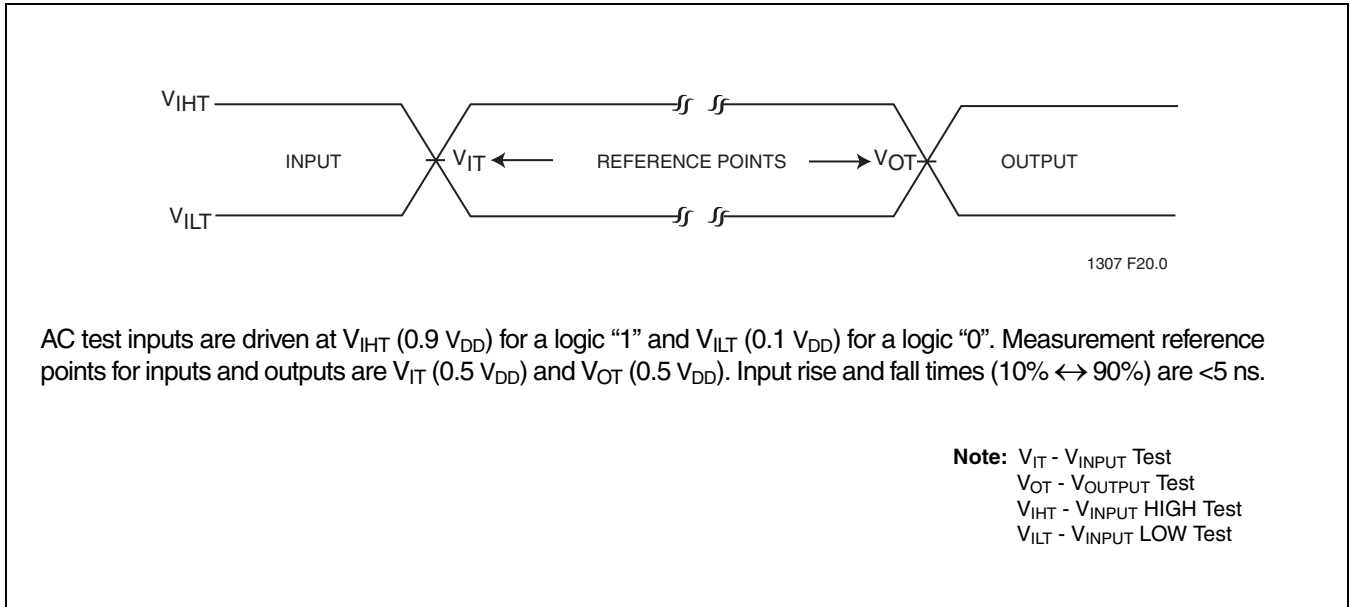


FIGURE 21: AC INPUT/OUTPUT REFERENCE WAVEFORMS

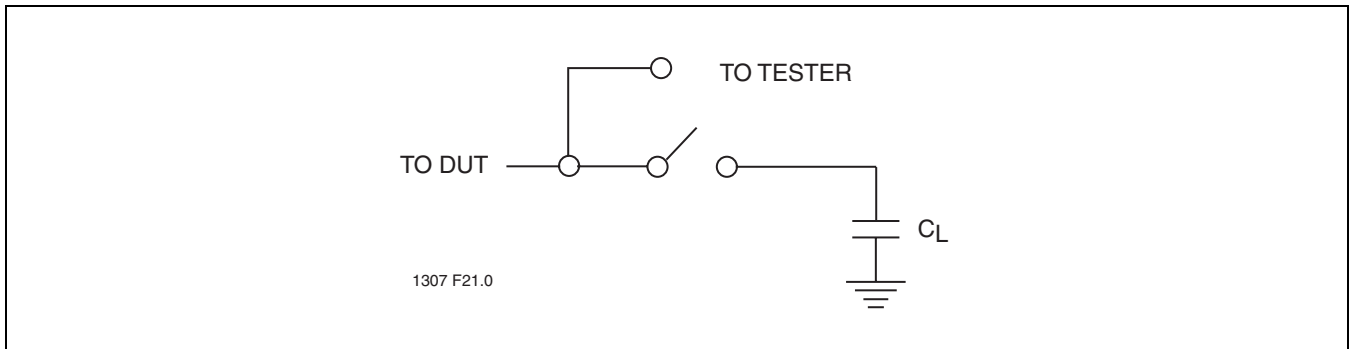
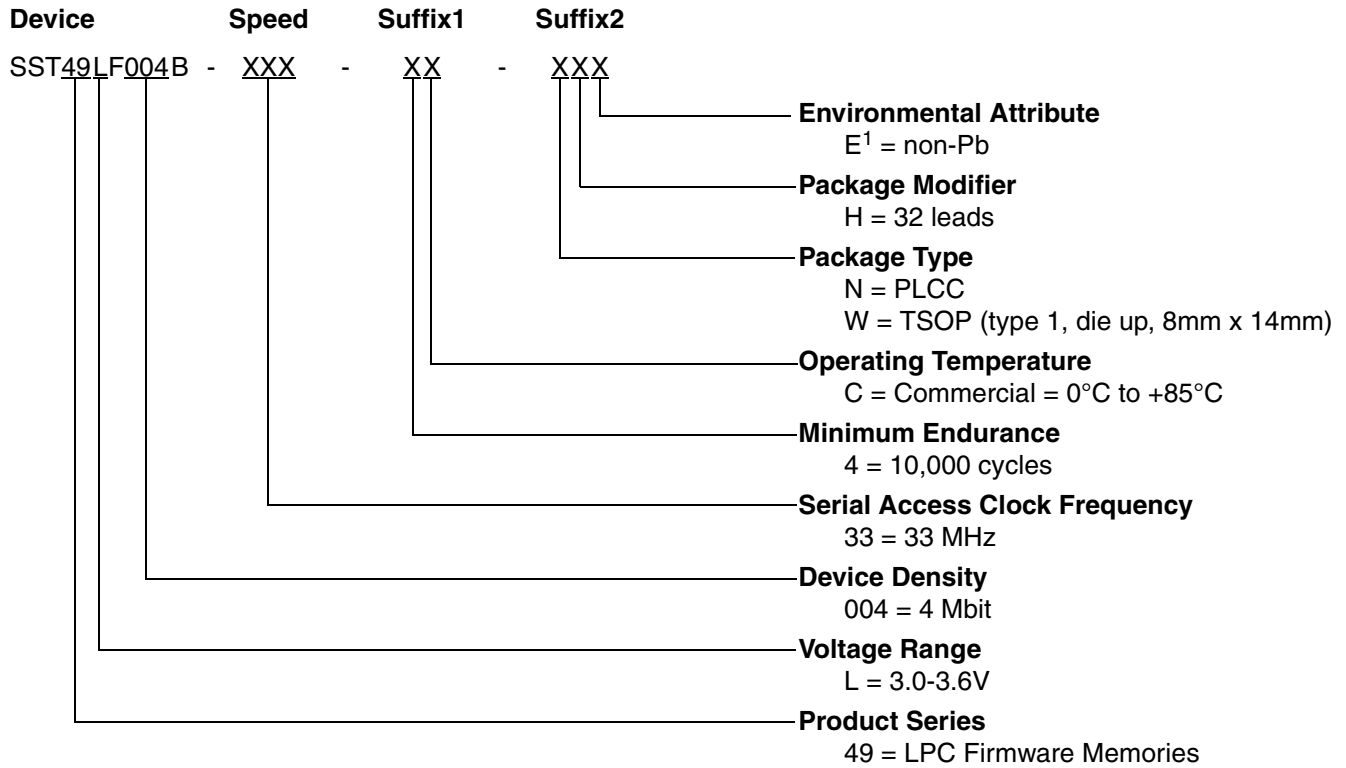


FIGURE 22: A TEST LOAD EXAMPLE



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**PRODUCT ORDERING INFORMATION**



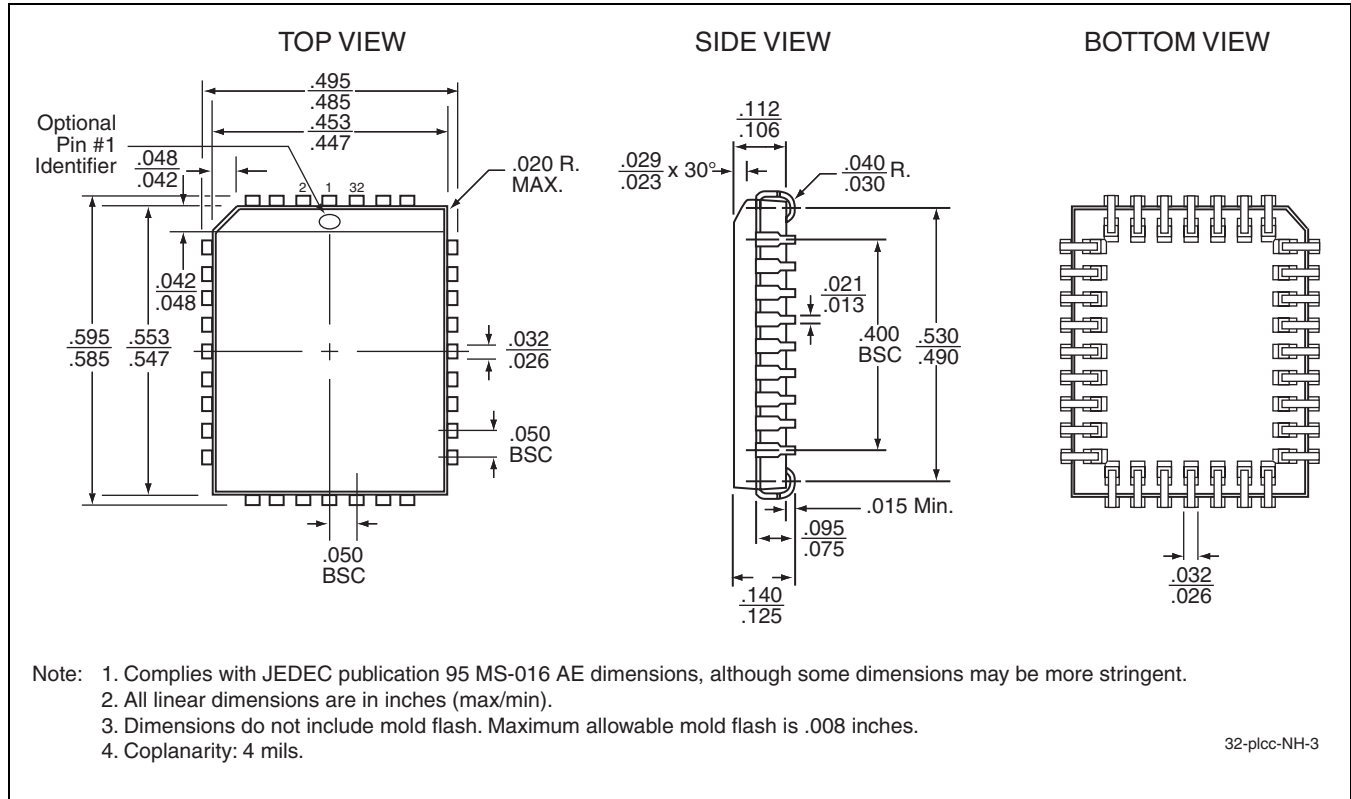
1. Environmental suffix "E" denotes non-Pb solder.  
SST non-Pb solder devices are "RoHS Compliant".

**Valid combinations for SST49LF004B**

SST49LF004B-33-4C-NHE SST49LF004B-33-4C-WHE

**Note:** Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.

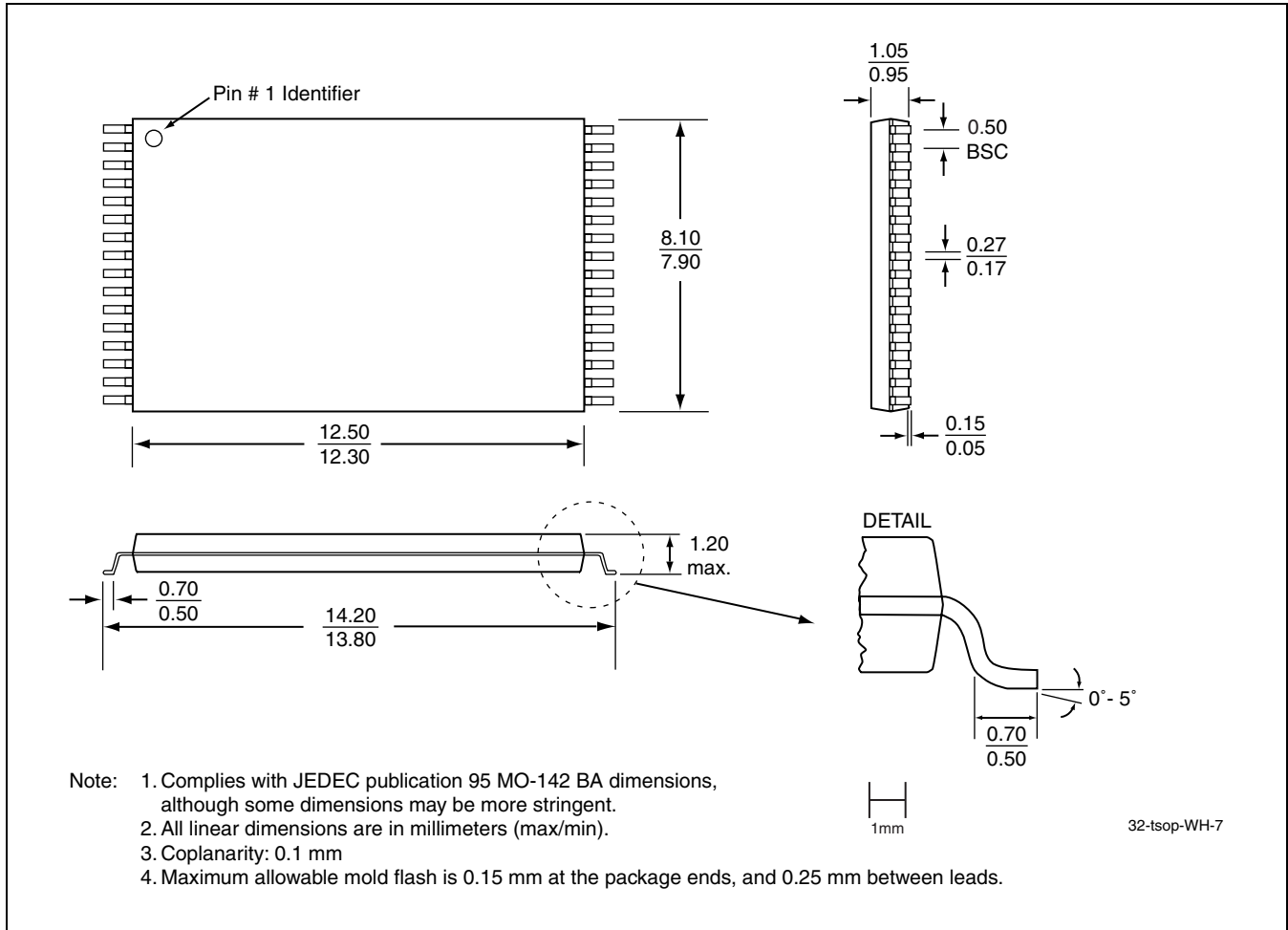
**PACKAGING DIAGRAMS**



**32-LEAD PLASTIC LEAD CHIP CARRIER (PLCC)**  
**SST PACKAGE CODE: NH**



Preliminary Specifications



**32-LEAD THIN SMALL OUTLINE PACKAGE (TSOP) 8MM X 14MM**  
**SST PACKAGE CODE: WH**

**TABLE 23: REVISION HISTORY**

Number	Description	Date
00	• Initial release	Oct 2005
01	• Updated Surface Mount Solder Reflow Temperature information • Added NH package information.	Jan 2006
02	• Cosmetic update to Figure 2	Feb 2006